PCN 15_0160

ADG5233/ADG5234 Data Sheet Changes

Rev. C to Rev. D

This document highlights the performance changes from the Rev. C to the Rev. D data sheet for the ADG5233 and ADG5234 Analog Multiplexers.

For full product information and changes to Typical Performance Characteristics plots please refer to the ADG5233/34 Rev. D data sheet.

1. HBM ESD

HBM ESD	Rev C	Rev D
I/O Port to Supplies	4 kV	8 kV
I/O Port to I/O Port	1 kV	2 kV
All other pins	4 kV	8 kV

2. Datasheet specification changes from Rev. C to Rev. D

Tables 1 to 4 outline a datasheet specification comparison of Rev. C to Rev. D material. The changed specifications are highlighted in red font.

SPECIFICATION CHANGES FROM Rev. C to Rev. D

Table 1. V_{DD} = +15 V ± 10%, V_{SS} = −15 V ± 10%, GND = 0 V, unless otherwise noted.

Parameter	Rev. C 25°C	Rev. C −40°C to +85°C	Rev. C −40°C to +125°C	Rev. D 25°C	Rev. D −40°C to +85°C	Rev. D −40°C to +125°C	Unit	Test Conditions/ Comments
ANALOG SWITCH								
Analog Signal Range			V_{DD} to V_{SS}			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	160			160			Ω typ	V_S = ±10 V, I_S = −1 mA
	200		250 280	200		250 280	Ω max	V_{DD} = +13.5 V, V_{SS} = −13.5 V
On-Resistance Match Between Channels, ΔR_{ON}	3.5			3.5			Ω typ	V_S = ±10 V, I_S = −1 mA
	8		9 10	8		9 10	Ω max	
On-Resistance Flatness, $R_{FLAT (ON)}$	38			38			Ω typ	V_S = ±10 V, I_S = −1 mA
	50		65 70	50		65 70	Ω max	
LEAKAGE CURRENTS								V_{DD} = +16.5 V, V_{SS} = −16.5 V
Source Off Leakage, I_S (Off)	±0.02			±0.02			nA typ	V_S = ±10 V, V_D = ±10 V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Drain Off Leakage, I_D (Off)	±0.02			±0.02			nA typ	V_S = ±10 V, V_D = ±10 V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.08			±0.08			nA typ	± V_S = V_D = ±10 V
	±0.2	±0.3	±0.9	±0.2	±0.3	±0.9	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			µA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1			±0.1	µA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
Dynamic Characteristics[1]								
Transition Time, $t_{TRANSITION}$	170			125			ns typ	R_L = 300 Ω, C_L = 35 pF
	210		250 280	160	190	215	ns max	V_S = 10 V
t_{ON} (EN)	175			145			ns typ	R_L = 300 Ω, C_L = 35 pF
	215		255 290	175	210	240	ns max	V_S = 10 V
t_{OFF} (EN)	80			125			ns typ	R_L = 300 Ω, C_L = 35 pF
	100		115 125	155	170	180	ns max	V_S = 10 V
Break-Before-Make Time Delay, t_D	60			45			ns typ	R_L = 300 Ω, C_L = 35 pF
			30			25	ns min	V_{S1} = V_{S2} = 10 V
Charge Injection, Q_{INJ}	−0.6			0.4			pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF
Off Isolation	−75			−76			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
Channel-to-Channel Crosstalk	−80			−87			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
−3 dB Bandwidth	205			355			MHz typ	R_L = 50 Ω, C_L = 5 pF
Insertion Loss	−6.3			−6.4			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
C_S (Off)	4.5			2.8			pF typ	V_S = 0 V, f = 1 MHz
C_D (Off)	10			9			pF typ	V_S = 0 V, f = 1 MHz
C_D (On), C_S (On)	15			13			pF typ	V_S = 0 V, f = 1 MHz
POWER REQUIREMENTS								V_{DD} = +16.5 V, V_{SS} = −16.5 V
I_{DD}	45			45			µA typ	Digital inputs = 0 V or V_{DD}
	55		70	55		70	µA max	
I_{SS}	0.001			0.001			µA typ	Digital inputs = 0 V or V_{DD}
			1			1	µA max	
V_{DD}/V_{SS}			±9/±22			±9/±22	V min/V max	GND = 0 V

[1] Guaranteed by design, not subject to production test.

Table 2. V_{DD} = +20V ± 10%, V_{SS} = −20 V ± 10%, GND = 0 V, unless otherwise noted.

Parameter	Rev. C 25°C	Rev. C −40°C to +85°C	Rev. C −40°C to +125°C	Rev. D 25°C	Rev. D −40°C to +85°C	Rev. D −40°C to +125°C	Unit	Test Conditions/ Comments
ANALOG SWITCH								
Analog Signal Range			V_{DD} to V_{SS}			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	140			140			Ω typ	V_S = ±15 V, I_S = −1 mA
	160	200	230	160	200	230	Ω max	V_{DD} = +18 V, V_{SS} = −18 V
On-Resistance Match Between Channels, ΔR_{ON}	3.5			3.5			Ω typ	V_S = ±15 V, I_S = −1 mA
	8	9	10	8	9	10	Ω max	
On-Resistance Flatness, $R_{FLAT (ON)}$	33			33			Ω typ	V_S = ±15 V, I_S = −1 mA
	45	55	60	45	55	60	Ω max	
LEAKAGE CURRENTS								V_{DD} = +22 V, V_{SS} = −22 V
Source Off Leakage, I_S (Off)	±0.02			±0.02			nA typ	V_S = ±15 V, V_D = ±15 V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Drain Off Leakage, I_D (Off)	±0.02			±0.02			nA typ	V_S = ±15 V, V_D = ±15 V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.08			±0.08			nA typ	± V_S = V_D = ±15 V
	±0.2	±0.3	±0.9	±0.2	±0.3	±0.9	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			µA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1			±0.1	µA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
Dynamic Characteristics[1]								
Transition Time, $t_{TRANSITION}$	170			125			ns typ	R_L = 300 Ω, C_L = 35 pF
	200	235	260	155	180	200	ns max	V_S = 10 V
t_{ON} (EN)	165			145			ns typ	R_L = 300 Ω, C_L = 35 pF
	200	240	265	170	200	220	ns max	V_S = 10 V
t_{OFF} (EN)	80			125			ns typ	R_L = 300 Ω, C_L = 35 pF
	95	105	115	155	160	170	ns max	V_S = 10 V
Break-Before-Make Time Delay, t_D	50			40			ns typ	R_L = 300 Ω, C_L = 35 pF
			30			20	ns min	V_{S1} = V_{S2} = 10 V
Charge Injection, Q_{INJ}	0			0.7			pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF
Off Isolation	−75			−76			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
Channel-to-Channel Crosstalk	−80			−87			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
−3 dB Bandwidth	210			370			MHz typ	R_L = 50 Ω, C_L = 5 pF
Insertion Loss	−5.5			−5.6			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
C_S (Off)	4.5			2.8			pF typ	V_S = 0 V, f = 1 MHz
C_D (Off)	10			9			pF typ	V_S = 0 V, f = 1 MHz
C_D (On), C_S (On)	15			13			pF typ	V_S = 0 V, f = 1 MHz
POWER REQUIREMENTS								V_{DD} = +22 V, V_{SS} = -22 V
I_{DD}	50			50			µA typ	Digital inputs = 0 V or V_{DD}
	70		110	70		110	µA max	
I_{SS}	0.001			0.001			µA typ	Digital inputs = 0 V or V_{DD}
			1			1	µA max	
V_{DD}/V_{SS}			±9/±22			±9/±22	V min/V max	GND = 0 V

1 Guaranteed by design, not subject to production test.

Table 3. V_{DD} = +12V ± 10%, V_{SS} = 0V GND = 0 V, unless otherwise noted.

Parameter	Rev. C 25°C	Rev. C −40°C to +85°C	Rev. C −40°C to +125°C	Rev. D 25°C	Rev. D −40°C to +85°C	Rev. D −40°C to +125°C	Unit	Test Conditions/ Comments
ANALOG SWITCH								
Analog Signal Range			0 V to V_{DD}			0 V to V_{DD}	V	
On Resistance, R_{ON}	360			360			Ω typ	V_S = 0 V to 10V, I_S = −1 mA
	500	610	700	500	610	700	Ω max	V_{DD} = +10.8V, V_{SS} = 0 V
On-Resistance Match Between Channels, ΔR_{ON}	5.5			5.5			Ω typ	V_S = 0 V to 10V, I_s = −1 mA
	20	21	22	20	21	22	Ω max	
On-Resistance Flatness, R_{FLAT} (ON)	170			170			Ω typ	V_S = 0 V to 10V, I_S = −1 mA
	280	335	370	280	335	370	Ω max	
LEAKAGE CURRENTS								V_{DD} = 13.2 V, V_{SS} = 0V
Source Off Leakage, I_S (Off)	±0.02			±0.02			nA typ	V_s = 1V/10V, V_D = +10 V/1V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Drain Off Leakage, I_D (Off)	±0.02			±0.02			nA typ	V_s = 1V/10V, V_D = +10 V/1V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.08			±0.08			nA typ	± V_S = V_D = 1 V/10V
	±0.2	±0.3	±0.9	±0.2	±0.3	±0.9	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			µA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1			±0.1	µA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
DYNAMIC CHARACTERISTICS[1]								
Transition Time, $t_{TRANSITION}$	235			165			ns typ	R_L = 300 Ω, C_L = 35 pF
	295	365	410	215	260	300	ns max	V_S = 8 V
t_{ON} (EN)	240			200			ns typ	R_L = 300 Ω, C_L = 35 pF
	305	380	430	245	305	350	ns max	V_S = 8 V
t_{OFF} (EN)	70			130			ns typ	R_L = 300 Ω, C_L = 35 pF
	90	105	115	165	180	200	ns max	V_S = 8 V
Break-Before-Make Time Delay, t_D	125			85			ns typ	R_L = 300 Ω, C_L = 35 pF
			65			45	ns min	V_{S1} = V_{S2} = 8 V
Charge Injection, Q_{INJ}	0			0			pC typ	V_S = 6 V, R_S = 0 Ω, C_L = 1 nF
Off Isolation	−75			−76			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
Channel-to-Channel Crosstalk	−80			−87			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
−3 dB Bandwidth	172			260			MHz typ	R_L = 50 Ω, C_L = 5 pF
Insertion Loss	−8.7			−9			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
C_S (Off)	5			3			pF typ	V_S = 0 V, f = 1 MHz
C_D (Off)	11			10			pF typ	V_S = 0 V, f = 1 MHz
C_D (On), C_S (On)	16			14			pF typ	V_S = 0 V, f = 1 MHz
POWER REQUIREMENTS								V_{DD} = 13.2
I_{DD}	40			40			µA typ	Digital inputs = 0 V or V_{DD}
	50		65	50		65	µA max	
V_{DD}			9/40			9/40	V min/V max	GND = 0 V, Vss=0V

1 Guaranteed by design, not subject to production test.

Table 4. V_{DD} = +36V ± 10%, V_{SS} = 0V GND = 0 V, unless otherwise noted.

Parameter	Rev. C 25°C	Rev. C −40°C to +85°C	Rev. C −40°C to +125°C	Rev. D 25°C	Rev. D −40°C to +85°C	Rev. D −40°C to +125°C	Unit	Test Conditions/ Comments
ANALOG SWITCH								
Analog Signal Range			0 V to V_{DD}			0 V to V_{DD}	V	
On Resistance, R_{ON}	140			140			Ω typ	V_S = ±10 V, I_S = −1 mA
	170	215	245	170	215	245	Ω max	V_{DD} = +13.5 V, V_{SS} = −13.5 V
On-Resistance Match Between Channels, ΔR_{ON}	3.5			3.5			Ω typ	V_S = ±10 V, I_S = −1 mA
	8	9	10	8	9	10	Ω max	
On-Resistance Flatness, R_{FLAT} (ON)	35			35			Ω typ	V_S = ±10 V, I_S = −1 mA
	50	60	65	50	60	65	Ω max	
LEAKAGE CURRENTS								V_{DD} = +16.5 V, V_{SS} = −16.5 V
Source Off Leakage, I_S (Off)	±0.02			±0.02			nA typ	V_S = ±10 V, V_D = ±10 V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Drain Off Leakage, I_D (Off)	±0.02			±0.02			nA typ	V_S = ±10 V, V_D = ±10 V
	±0.1	±0.2	±0.4	±0.1	±0.2	±0.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.08			±0.08			nA typ	±V_S = V_D = ±10 V
	±0.2	±0.3	±0.9	±0.2	±0.3	±0.9	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			µA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1			±0.1	µA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
Dynamic Characteristics[1]								
Transition Time, $t_{TRANSITION}$	205			155			ns typ	R_L = 300 Ω, C_L = 35 pF
	255	275	290	200	215	230	ns max	V_S = 10 V
t_{ON} (EN)	200			180			ns typ	R_L = 300 Ω, C_L = 35 pF
	240	265	290	215	235	250	ns max	V_S = 10 V
t_{OFF} (EN)	85			150			ns typ	R_L = 300 Ω, C_L = 35 pF
	115	115	115	190	190	190	ns max	V_S = 10 V
Break-Before-Make Time Delay, t_D	65			50			ns typ	R_L = 300 Ω, C_L = 35 pF
			35			25	ns min	V_{S1} = V_{S2} = 10 V
Charge Injection, Q_{INJ}	−0.6			0.5			pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF
Off Isolation	−75			−76			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
Channel-to-Channel Crosstalk	−80			−87			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
−3 dB Bandwidth	190			275			MHz typ	R_L = 50 Ω, C_L = 5 pF
Insertion Loss	−5.9			−6.2			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz
C_S (Off)	4.5			2.8			pF typ	V_S = 0 V, f = 1 MHz
C_D (Off)	10			9			pF typ	V_S = 0 V, f = 1 MHz
C_D (On), C_S (On)	15			13			pF typ	V_S = 0 V, f = 1 MHz
POWER REQUIREMENTS								V_{DD} = +16.5 V, V_{SS} = −16.5 V
I_{DD}	80			80			µA typ	Digital inputs = 0 V or V_{DD}
	100		130	100		130	µA max	
V_{DD}			9/40			9/40	V min/V max	GND = 0 V, Vss=0V

1 Guaranteed by design, not subject to production test.